

# November 1999 ADVANCE INFORMATION

# FDC602P

# P-Channel 2.5V Specified PowerTrench® MOSFET

# **General Description**

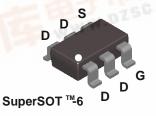
This P-Channel 2.5V specified MOSFET uses a rugged gate version of Fairchild's advanced PowerTrench process. It has been optimized for power management applications with a wide range of gate drive voltage (2.5V – 12V).

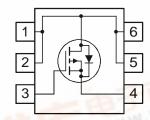
## **Applications**

- · Battery management
- Load switch
- Battery protection

### **Features**

- -5.5 A, -12 V  $R_{DS(ON)} = 0.033 \Omega$  @  $V_{GS} = -4.5 \text{ V}$   $R_{DS(ON)} = 0.052 \Omega$  @  $V_{GS} = -2.5 \text{ V}$
- · Fast switching speed.
- High performance trench technology for extremely low R<sub>DS(ON)</sub>.





Absolute Maximum Ratings TA=25°C unless otherwise noted

Symbol	Parameter		Ratings		
V <sub>DSS</sub>	Drain-Source Voltage	M.	-12	V	
V <sub>GSS</sub>	Gate-Source Voltage	,	±12	V	
I <sub>D</sub>	Drain Current - Continuous	(Note 1a)	-5.5	А	
	- Pulsed		-30		
P <sub>D</sub>	Maximum Power Dissipation	(Note 1a)	1.6	W	
		(Note 1b)	0.8	an tor	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Tem	perature Range	-55 to +150	°C	

# **Thermal Characteristics**

R <sub>θJA</sub>	Thermal Resistance, Junction-to-Ambient	(Note 1a)	78	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	(Note 1)	30	°C/W

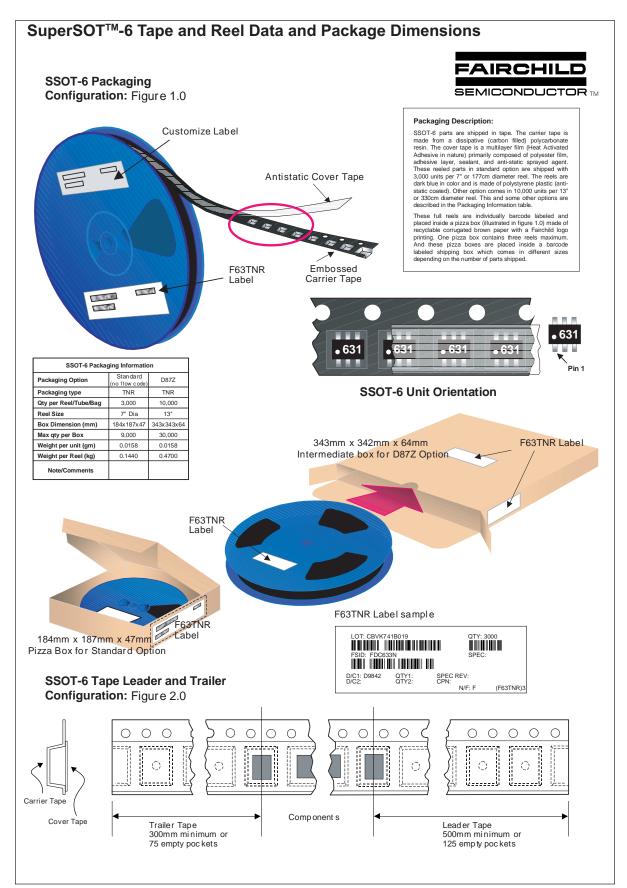
Package Marking and Ordering Information

Device Marking	evice Marking Device		Tape width	Quantity	
.602	FDC602P	7"	8mm	3000 units	

Electrical Characteristics T <sub>A</sub> = 25°C unless otherwise noted										
Symbol	Parameter	Min	Тур	Max	Units					
Off Char	acteristics		•			•				
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$	-12			V				
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS} = -10 \text{ V},  V_{GS} = 0 \text{ V}$			-1	μΑ				
I <sub>GSSF</sub>	Gate-Body Leakage, Forward	$V_{GS} = 12 \text{ V}, \qquad V_{DS} = 0 \text{ V}$			100	nA				
I <sub>GSSR</sub>	Gate-Body Leakage, Reverse	$V_{GS} = -12 \text{ V}$ $V_{DS} = 0 \text{ V}$			-100	nA				
	acteristics (Note 2)	I		ı						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	-0.6		-1.5	V				
$R_{\text{DS(on)}}$	Static Drain–Source On–Resistance	$V_{GS} = -4.5 \text{ V}, \qquad I_{D} = -5.5 \text{ A}$ $V_{GS} = -2.5 \text{ V}, \qquad I_{D} = -4.4 \text{ A}$			0.033 0.052	Ω				
Drain-S	ource Diode Characteristics a	and Maximum Ratings								
Is	Maximum Continuous Drain-Source	Diode Forward Current			-1.3	Α				
$V_{SD}$	Drain–Source Diode Forward Voltage	$V_{GS} = 0 \text{ V},  I_S = -1.3 \text{ A (Note 2)}$			-1.2	V				

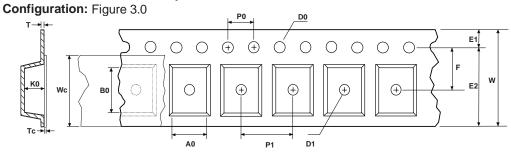
#### Notes

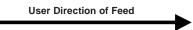
- 1.  $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.
  - a.  $78^{\circ}\text{C/W}$  when mounted on a  $1\text{in}^2$  pad of 2oz copper on FR-4 board.
  - b. 156°C/W when mounted on a minimum pad.
- 2. Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%



# SuperSOT<sup>™</sup>-6 Tape and Reel Data and Package Dimensions, continued

### **SSOT-6 Embossed Carrier Tape**



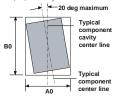


Dimensions are in millimeter														
Pkg type	A0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	т	Wc	Тс
SSOT-6 (8mm)	3.23 +/-0.10	3.18 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.37 +/-0.10	0.255 +/-0.150	5.2 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation



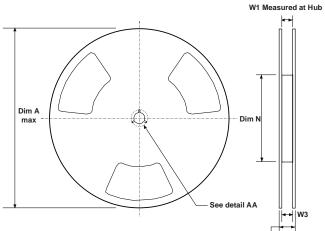
Sketch B (Top View)
Component Rotation



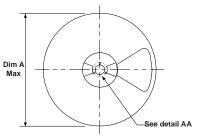
Sketch C (Top View)

Component lateral movement

# SSOT-6 Reel Configuration: Figure 4.0





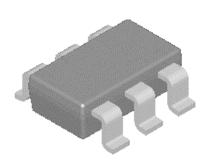


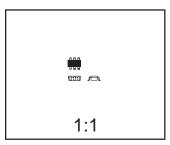
# 7" Diameter Option B Min Dim D DETAIL AA

	Dimensions are in inches and millimeters								
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9

# SuperSOT<sup>™</sup>-6 Tape and Reel Data and Package Dimensions, continued

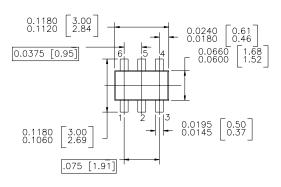
# SuperSOT -6 (FS PKG Code 31, 33)

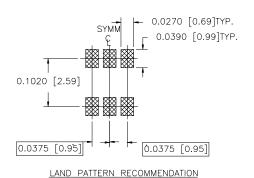




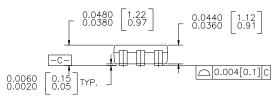
Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

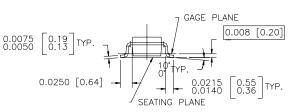
Part Weight per unit (gram): 0.0158





CONTROLLING DIMENSION IS INCH VALUES IN [ ] ARE MILLIMETERS





NOTES: UNLESS OTHERWISE SPECIFIED

1.0 STANDARD LEAD FINISH: 150 MICROINCHES 93.81 MICROMETERS) MINIMUM TIN / LEAD (SOLDER) ON COPPER.

2.0 NO JEDEC REGISTRATION AS OF JULY 1996

SUPER SOT 6 LEADS



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